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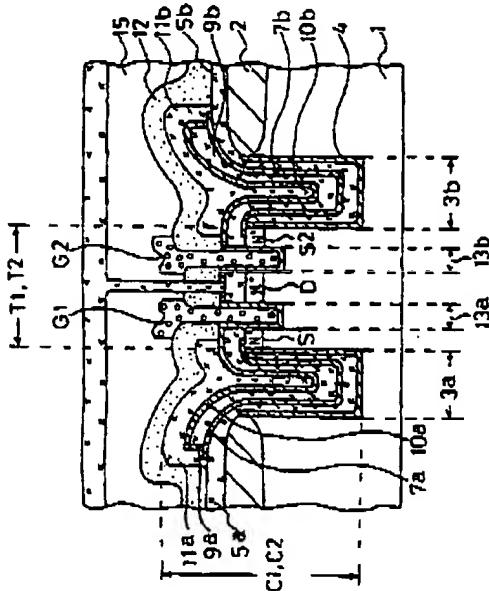
APPLICATION DATE : 18-01-89
 APPLICATION NUMBER : 01010310

APPLICANT : SANYO ELECTRIC CO LTD;

INVENTOR : MIYAWAKI YOSHIHIKO;

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TITLE : SEMICONDUCTOR STORAGE DEVICE
 AND MANUFACTURE THEREOF



ABSTRACT : PURPOSE: To eliminate the need for isolation through a photolithographic technique on the bases of trench sections, and to double storage capacitance by forming a first storage capacitor shaped into the first trench section and a second storage capacitor formed into the second trench section.

CONSTITUTION: Storage capacitors C1, C2 are formed into first trench sections 3a, 3b holding transfer transistors T1, T2. Consequently, the first storage capacitor C1 in the first trench section 3a and the second storage capacitor C2 in the second trench section 3b can be made unrelated to the size of a distance between cells. Accordingly, a photolithographic technique having high accuracy, by which polysilicon layers on the bases of the first trench section 3a and the second trench section 3b are removed selectively, need not be used. When storage electrodes 9a, 9b are employed as common storage electrodes, storage capacitance can be doubled respectively.

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